



Product data sheet

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Features

- 340 Watts peak pulse power (tp = $8/20\mu s$)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Protection two data lines:
- IEC 61000-4-2 ±8kV contact ±15kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 12A (8/20µs)

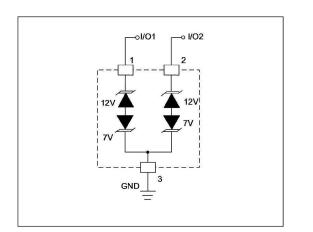
Mechanical Data

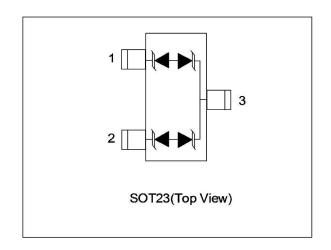
- SOT-23 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Applications

- Dataline
- Automatic Teller Machines
- Net works
- Power line

Schematic & PIN Configuration







SOT-23





Absolute Maximum Rating

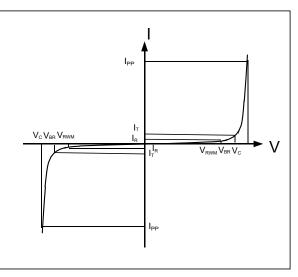
Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20 \mu s$)	P _{PP}	340	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I _{pp}	12	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	15 8	kV
Lead Soldering Temperature	TL	260(10seconds)	°C
Junction Temperature	TJ	-55 to + 125	°C
Storage Temperature	T _{stg}	-55 to + 125	°C

Electrical Characteristics

			Pins 1 to 3 and 2 to 3 (12V TVS)		Pins 3 to 1 and 3 to 2 (7V TVS)				
Parameter	Symbol	Conditions	Min	Typical	Max	Min	Typical	Max	Units
Reverse Stand-Off Voltage	Vrwm				12			7	V
Reverse Breakdown Voltage	VBR	IT=1mA	13.3			7.5			V
Reverse Leakage Current	Ir	VR=VRWM			1			1	μΑ
Clamping Voltage	VC	IPP=12A,tp=8/20µs		28					V
Clamping Voltage	Vc	IPP=20A,tp=8/20µs					20		V
Junction Capacitance	Cj	$V_R = 0V, f = 1MHz$		30			30		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter	
Ipp	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
VRWM	Working Peak Reverse Voltage	
Ir	Maximum Reverse Leakage Current @ VRWM	
VBR	Breakdown Voltage @ IT	
IT Test Current		



Note:. $8/20\mu s$ pulse waveform.





Typical Characteristics

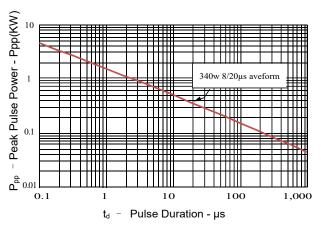


Figure 1: Peak Pulse Power vs. Pulse Time

Figure 2: Power Derating Curve

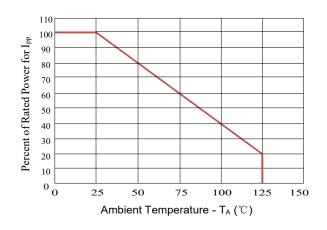
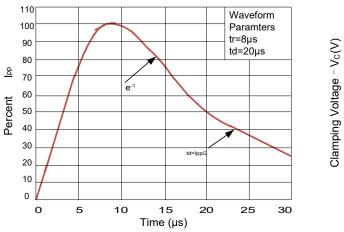
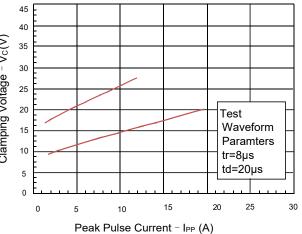


Figure3: Pulse Waveform

Figure 4: Clamping Voltage vs.lpp

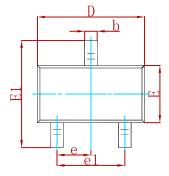


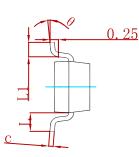


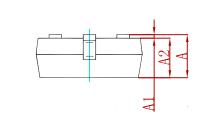




PACKAGE MECHANICAL DATA

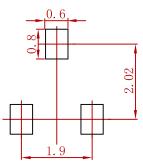






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

Controlling dimension:in millimeters.
General tolerance:± 0.05mm.
The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SM712.TCT	SOT-23	3000



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